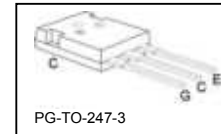
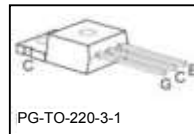
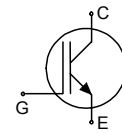


Fast IGBT in NPT-technology

- 75% lower E_{off} compared to previous generation combined with low conduction losses
- Short circuit withstand time – 10 μ s
- Designed for:
 - Motor controls
 - Inverter
- NPT-Technology for 600V applications offers:
 - very tight parameter distribution
 - high ruggedness, temperature stable behaviour
 - parallel switching capability



- Qualified according to JEDEC¹ for target applications
- Pb-free lead plating; RoHS compliant
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>

Type	V_{CE}	I_C	$V_{CE(sat)}$	T_j	Marking	Package
SGP20N60	600V	20A	2.4V	150°C	G20N60	PG-TO-220-3-1
SGW20N60	600V	20A	2.4V	150°C	G20N60	PG-TO-247-3

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current	I_C	40	A
$T_C = 25^\circ\text{C}$		20	
$T_C = 100^\circ\text{C}$		80	
Pulsed collector current, t_p limited by T_{jmax}	I_{Cpuls}	80	
Turn off safe operating area	-	80	
$V_{CE} \leq 600\text{V}$, $T_j \leq 150^\circ\text{C}$			
Gate-emitter voltage	V_{GE}	± 20	V
Avalanche energy, single pulse	E_{AS}	115	mJ
$I_C = 20\text{ A}$, $V_{CC} = 50\text{ V}$, $R_{GE} = 25\ \Omega$, start at $T_j = 25^\circ\text{C}$			
Short circuit withstand time ²	t_{SC}	10	μ s
$V_{GE} = 15\text{V}$, $V_{CC} \leq 600\text{V}$, $T_j \leq 150^\circ\text{C}$			
Power dissipation	P_{tot}	179	W
$T_C = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j , T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wavesoldering, 1.6mm (0.063 in.) from case for 10s	T_s	260	

¹ J-STD-020 and JESD-022

² Allowed number of short circuits: <1000; time between short circuits: >1s.

Thermal Resistance

Parameter	Symbol	Conditions	Max. Value	Unit
Characteristic				
IGBT thermal resistance, junction – case	R_{thJC}		0.7	K/W
Thermal resistance, junction – ambient	R_{thJA}	PG-TO-220-3-1 PG-TO-247-3-21	62 40	

Electrical Characteristic, at $T_j = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Static Characteristic						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	600	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=20A$ $T_J=25^{\circ}C$ $T_J=150^{\circ}C$	1.7 -	2 2.4	2.4 2.9	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=700\mu A, V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$ $T_J=25^{\circ}C$ $T_J=150^{\circ}C$	- -	- -	40 2500	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	g_{fs}	$V_{CE}=20V, I_C=20A$	-	14	-	S
Dynamic Characteristic						
Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$	-	1100	1320	pF
Output capacitance	C_{oss}		-	107	128	
Reverse transfer capacitance	C_{rss}		-	63	76	
Gate charge	Q_{Gate}	$V_{CC}=480V, I_C=20A$ $V_{GE}=15V$	-	100	130	nC
Internal emitter inductance	L_E	PG-TO-220-3-1	-	7	-	nH
measured 5mm (0.197 in.) from case		PG-TO-247-3-21	-	13	-	
Short circuit collector current ²⁾	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $V_{CC}\leq 600V,$ $T_J\leq 150^{\circ}C$	-	200	-	A

²⁾ Allowed number of short circuits: <1000; time between short circuits: >1s.

Switching Characteristic, Inductive Load, at $T_j=25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=25^{\circ}\text{C}$, $V_{CC}=400\text{V}$, $I_C=20\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=16\Omega$, $L_{\sigma}^{1)}=180\text{nH}$, $C_{\sigma}^{1)}=900\text{pF}$	-	36	46	ns
Rise time	t_r		-	30	36	
Turn-off delay time	$t_{d(off)}$		-	225	270	
Fall time	t_f		-	54	65	
Turn-on energy	E_{on}	Energy losses include “tail” and diode reverse recovery.	-	0.44	0.53	mJ
Turn-off energy	E_{off}		-	0.33	0.43	
Total switching energy	E_{ts}		-	0.77	0.96	

Switching Characteristic, Inductive Load, at $T_j=150^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
IGBT Characteristic						
Turn-on delay time	$t_{d(on)}$	$T_j=150^{\circ}\text{C}$ $V_{CC}=400\text{V}$, $I_C=20\text{A}$, $V_{GE}=0/15\text{V}$, $R_G=16\Omega$, $L_{\sigma}^{1)}=180\text{nH}$, $C_{\sigma}^{1)}=900\text{pF}$ Energy losses include “tail” and diode reverse recovery.	-	36	46	ns
Rise time	t_r		-	30	36	
Turn-off delay time	$t_{d(off)}$		-	250	300	
Fall time	t_f		-	63	76	
Turn-on energy	E_{on}		-	0.67	0.81	mJ
Turn-off energy	E_{off}		-	0.49	0.64	
Total switching energy	E_{ts}		-	1.12	1.45	

¹⁾ Leakage inductance L_{σ} and Stray capacity C_{σ} due to dynamic test circuit in Figure E.

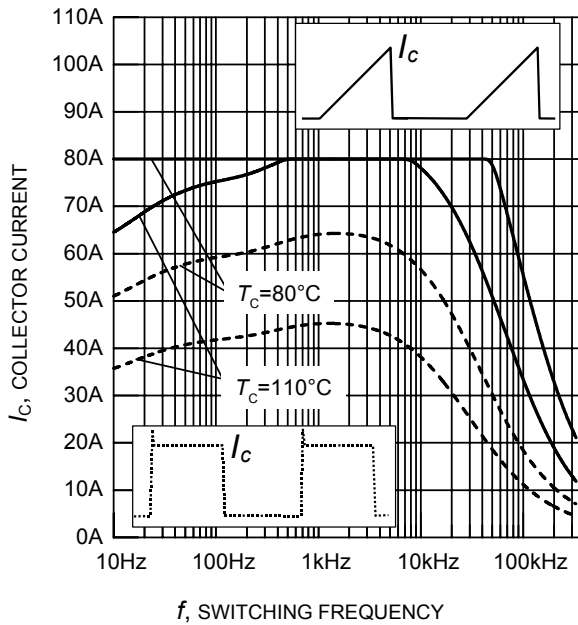


Figure 1. Collector current as a function of switching frequency

($T_j \leq 150^\circ\text{C}$, $D = 0.5$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 16\Omega$)

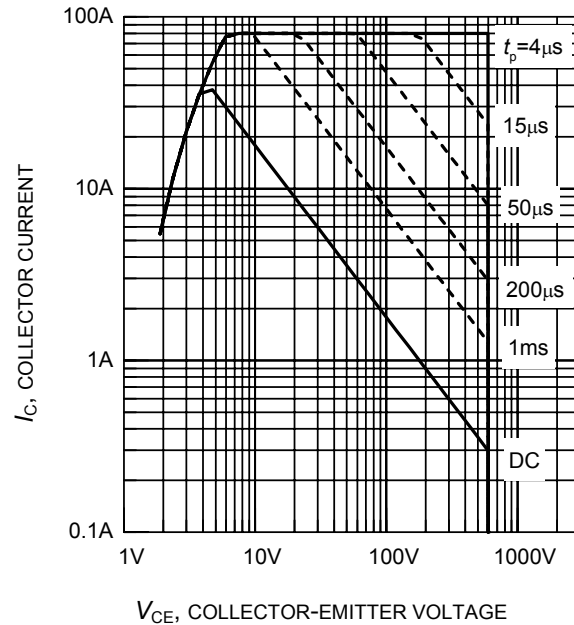


Figure 2. Safe operating area

($D = 0$, $T_C = 25^\circ\text{C}$, $T_j \leq 150^\circ\text{C}$)

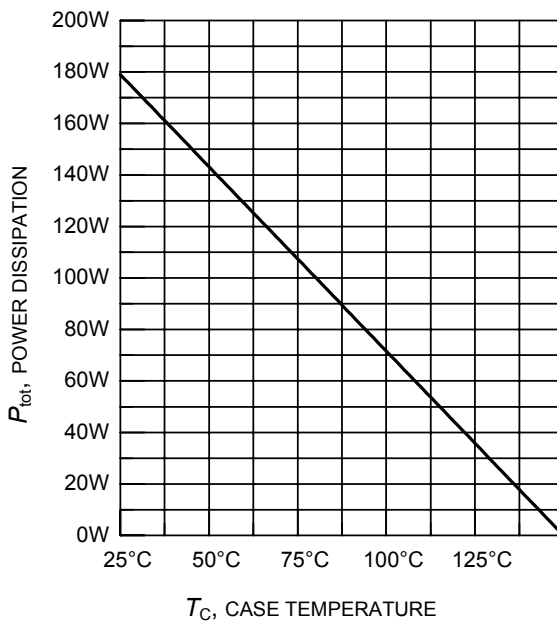


Figure 3. Power dissipation as a function of case temperature

($T_j \leq 150^\circ\text{C}$)

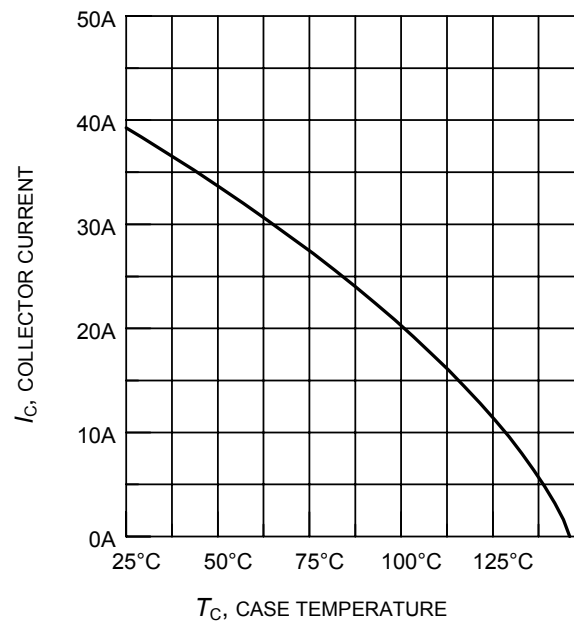


Figure 4. Collector current as a function of case temperature

($V_{GE} \leq 15\text{V}$, $T_j \leq 150^\circ\text{C}$)

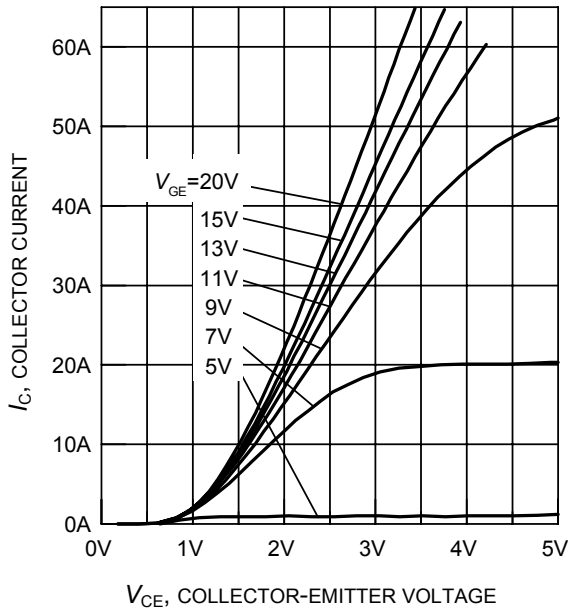


Figure 5. Typical output characteristics
($T_j = 25^\circ\text{C}$)

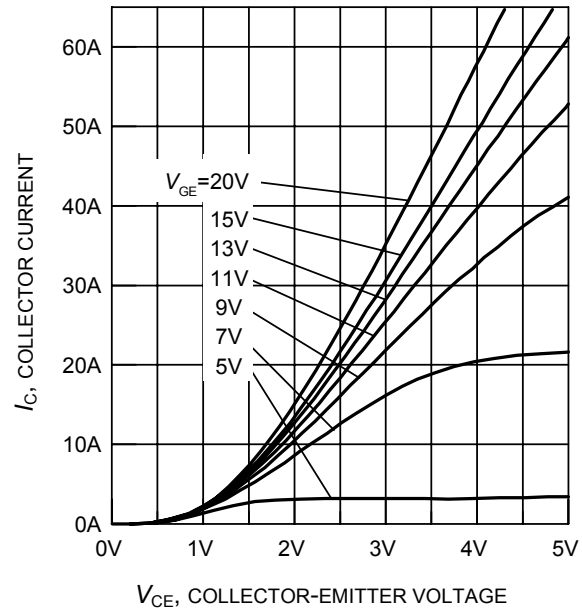


Figure 6. Typical output characteristics
($T_j = 150^\circ\text{C}$)

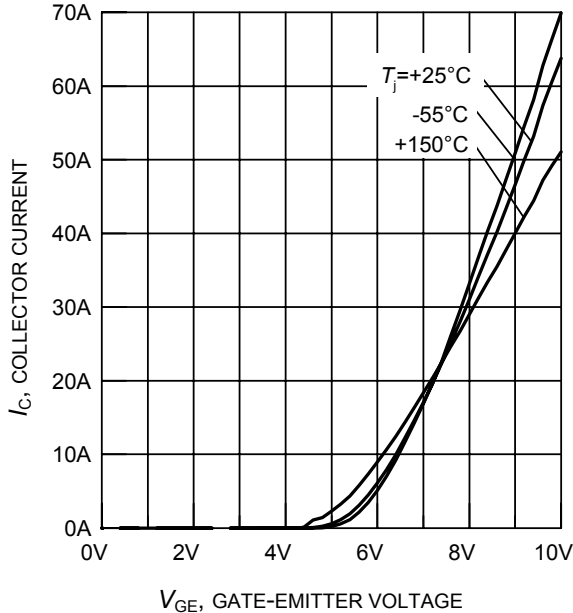


Figure 7. Typical transfer characteristics
($V_{ce} = 10\text{V}$)

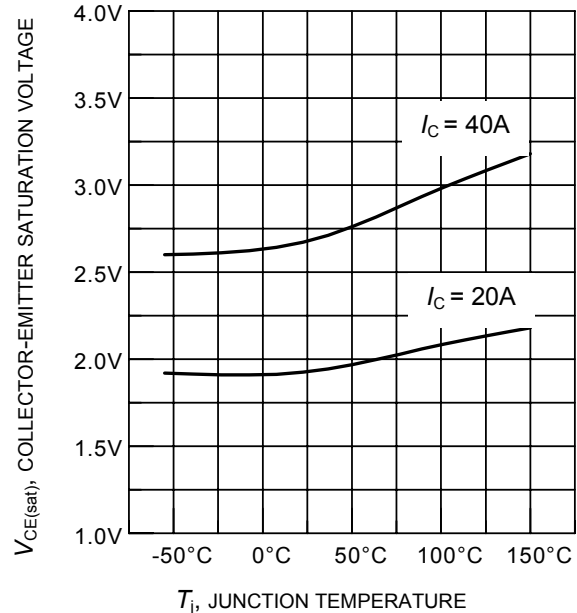


Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature
($V_{ge} = 15\text{V}$)

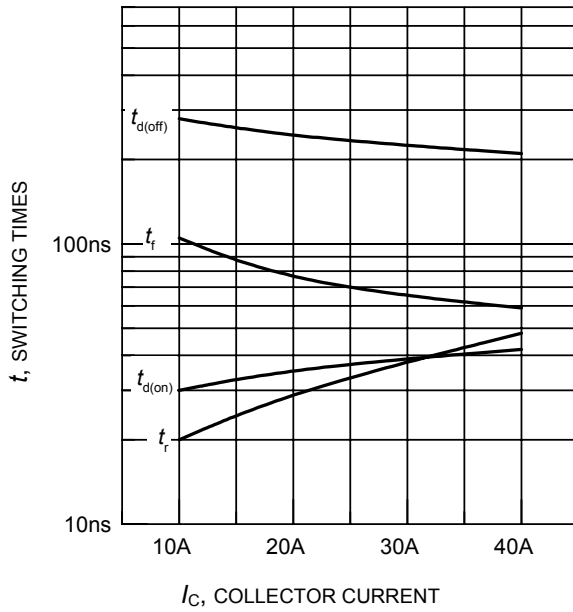


Figure 9. Typical switching times as a function of collector current
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 16\Omega$, Dynamic test circuit in Figure E)

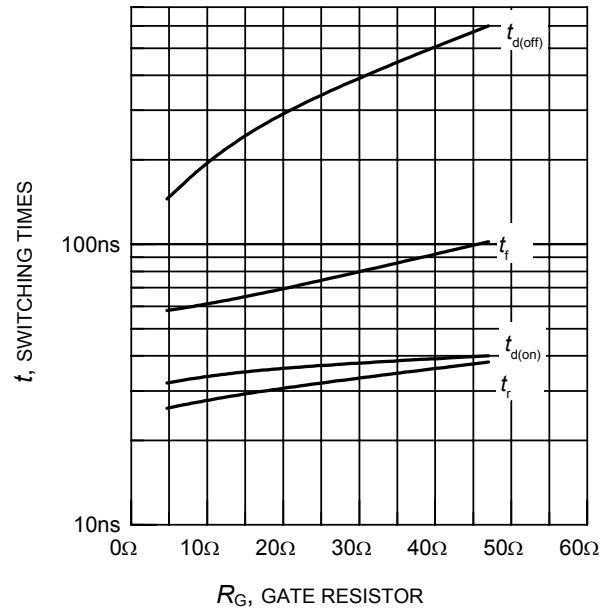


Figure 10. Typical switching times as a function of gate resistor
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 20\text{A}$, Dynamic test circuit in Figure E)

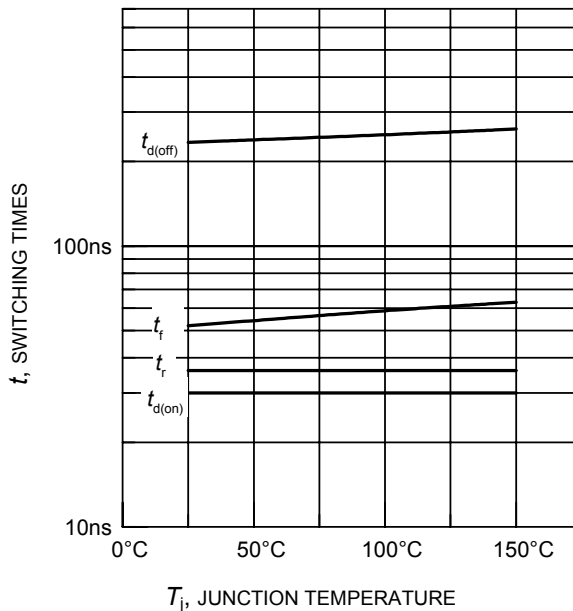


Figure 11. Typical switching times as a function of junction temperature
(inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 20\text{A}$, $R_G = 16\Omega$, Dynamic test circuit in Figure E)

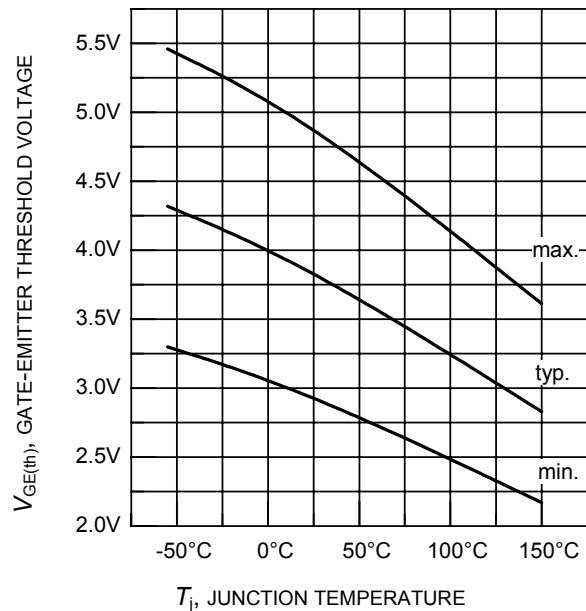


Figure 12. Gate-emitter threshold voltage as a function of junction temperature
($I_C = 0.7\text{mA}$)

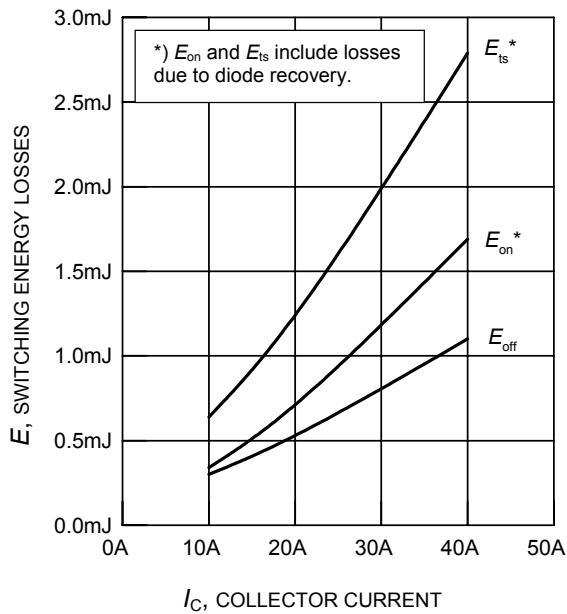


Figure 13. Typical switching energy losses as a function of collector current
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $R_G = 16\Omega$, Dynamic test circuit in Figure E)

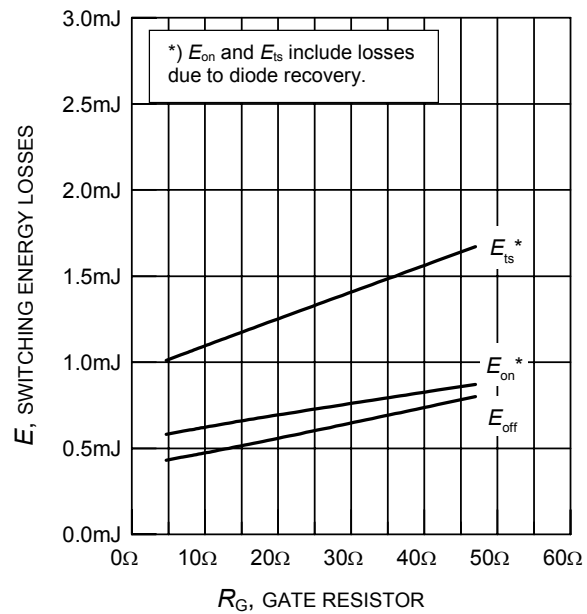


Figure 14. Typical switching energy losses as a function of gate resistor
(inductive load, $T_j = 150^\circ\text{C}$, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 20\text{A}$, Dynamic test circuit in Figure E)

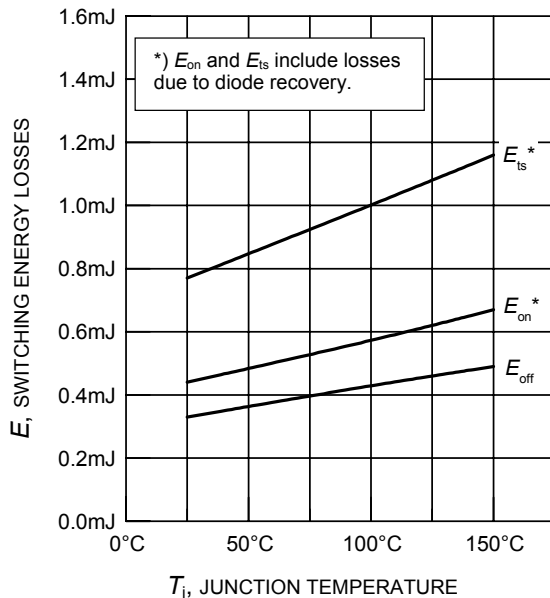


Figure 15. Typical switching energy losses as a function of junction temperature
(inductive load, $V_{CE} = 400\text{V}$, $V_{GE} = 0/+15\text{V}$, $I_C = 20\text{A}$, $R_G = 16\Omega$, Dynamic test circuit in Figure E)

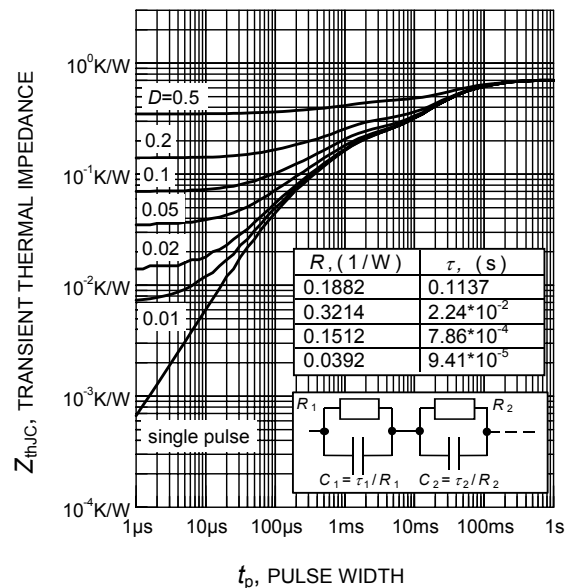


Figure 16. IGBT transient thermal impedance as a function of pulse width
($D = t_p / T$)

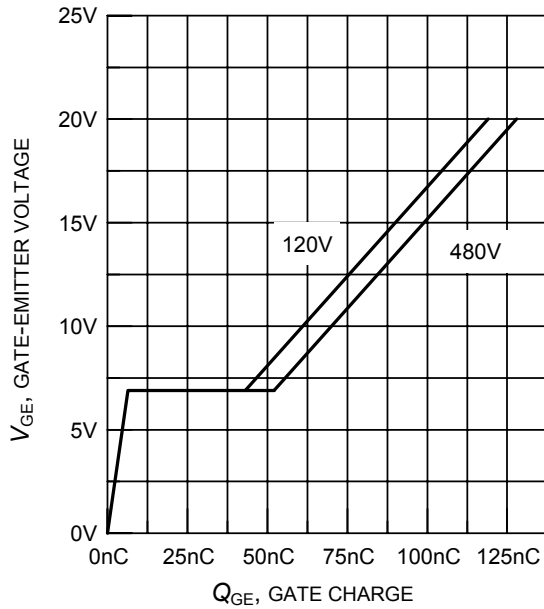


Figure 17. Typical gate charge
($I_C = 20A$)

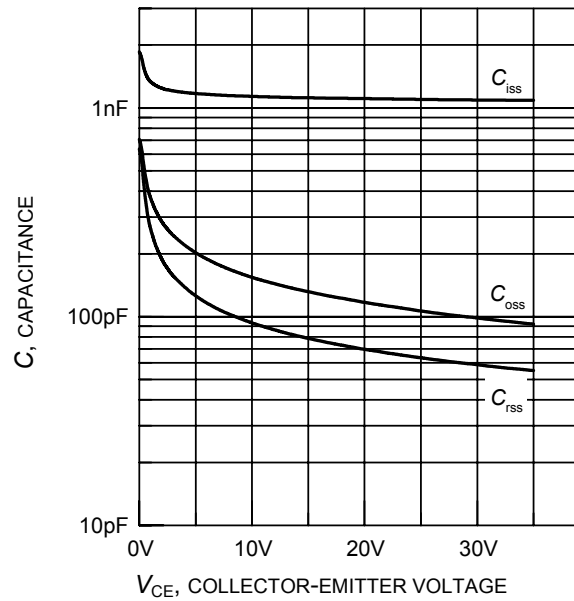


Figure 18. Typical capacitance as a function of collector-emitter voltage
($V_{GE} = 0V$, $f = 1MHz$)

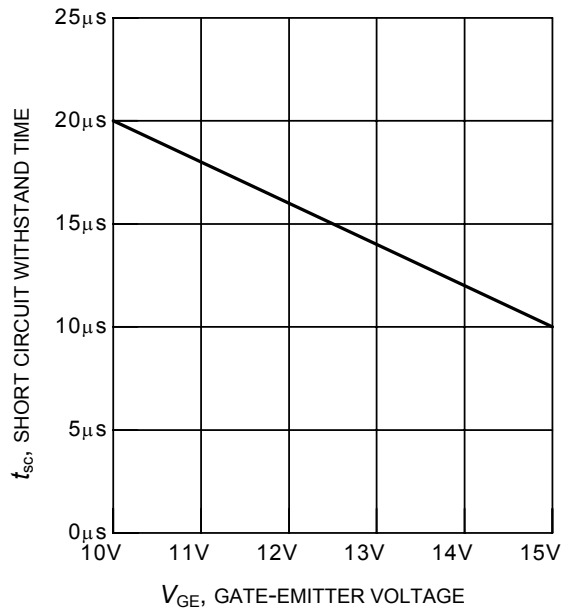


Figure 19. Short circuit withstand time as a function of gate-emitter voltage
($V_{CE} = 600V$, start at $T_j = 25^\circ C$)

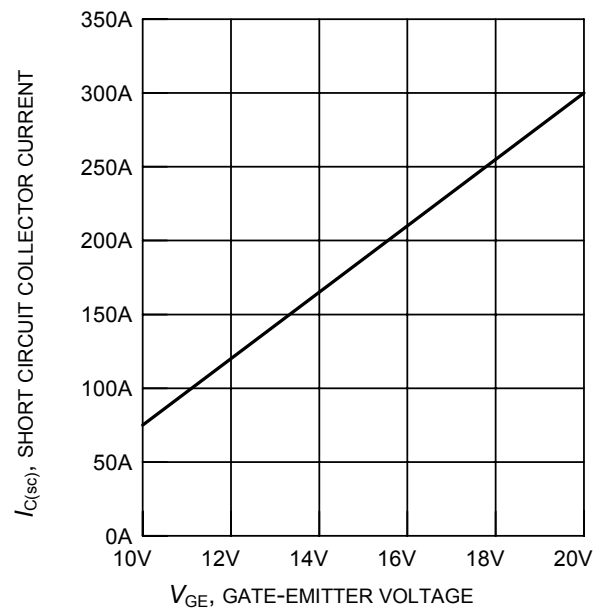
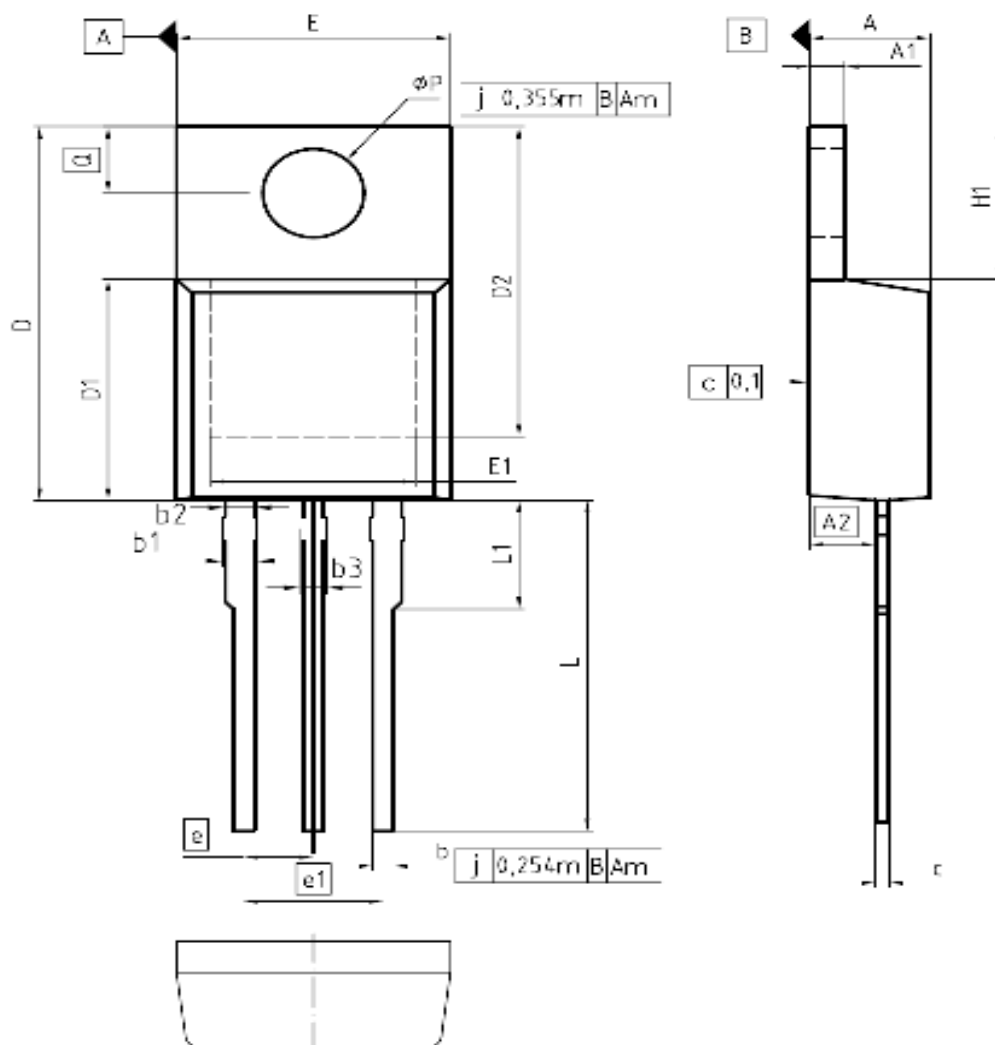
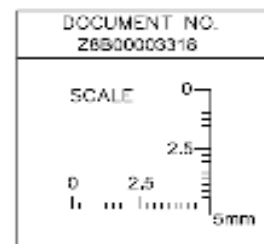


Figure 20. Typical short circuit collector current as a function of gate-emitter voltage
($V_{CE} \leq 600V$, $T_j = 150^\circ C$)

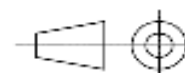
PG-TO220-3-1



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,50	4,57	0,189	0,180
A1	1,17	1,40	0,046	0,055
A2	2,15	2,72	0,085	0,107
b	0,85	0,86	0,026	0,034
b1	0,95	1,40	0,037	0,055
b2	0,95	1,15	0,037	0,045
b3	0,85	1,15	0,026	0,045
c	0,33	0,80	0,013	0,024
D	14,81	15,95	0,583	0,628
D1	8,51	9,45	0,335	0,372
D2	12,19	13,10	0,480	0,516
E	9,70	10,36	0,382	0,408
E1	6,50	6,80	0,256	0,339
e	2,54		0,100	
e1	5,08		0,200	
N	3		3	
H1	5,90	6,90	0,232	0,272
L	13,00	14,00	0,512	0,551
L1	-	4,60	-	0,189
ϕP	3,80	3,89	0,142	0,153
Q	2,50	3,00	0,102	0,118



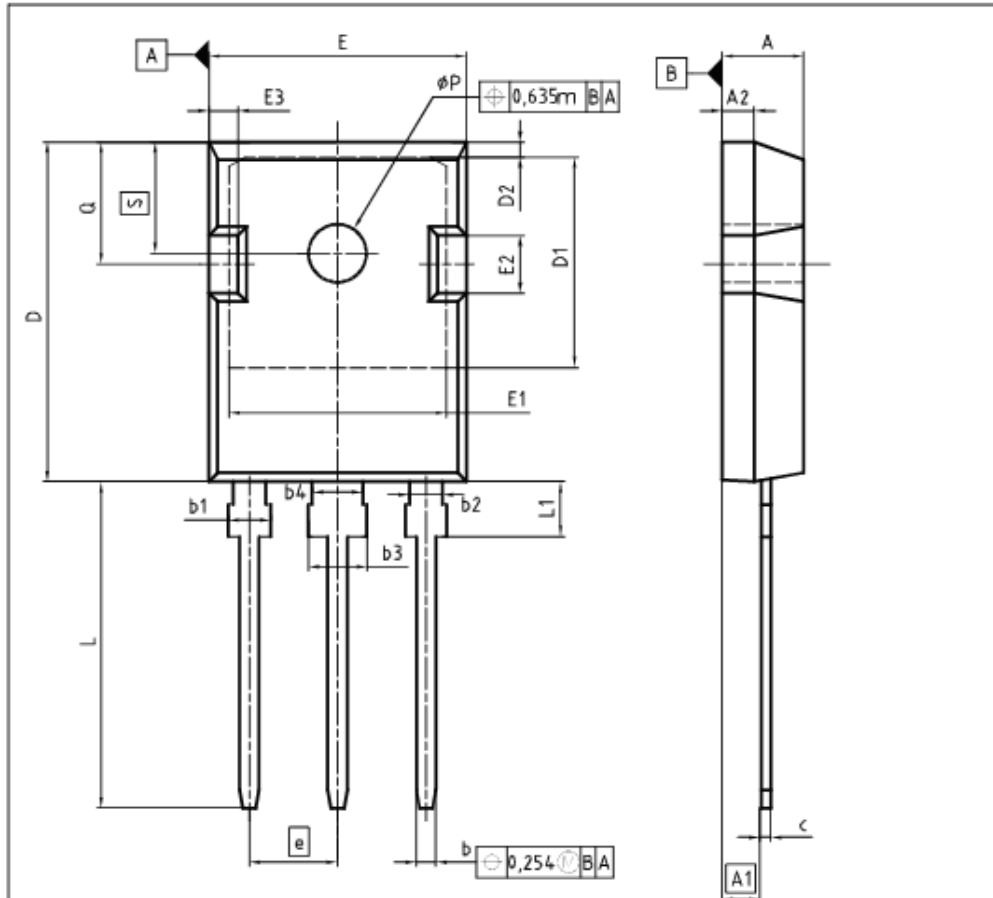
EUROPEAN PROJECTION



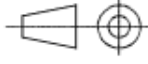
ISSUE DATE
23-08-2007

REVISION
05

T0247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.63	5.21	0.180	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.36	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44		0.214	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
ϕP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

DOCUMENT NO. Z8B00003327
SCALE 0 5 7.5mm
EUROPEAN PROJECTION 
ISSUE DATE 01-10-2009
REVISION 04

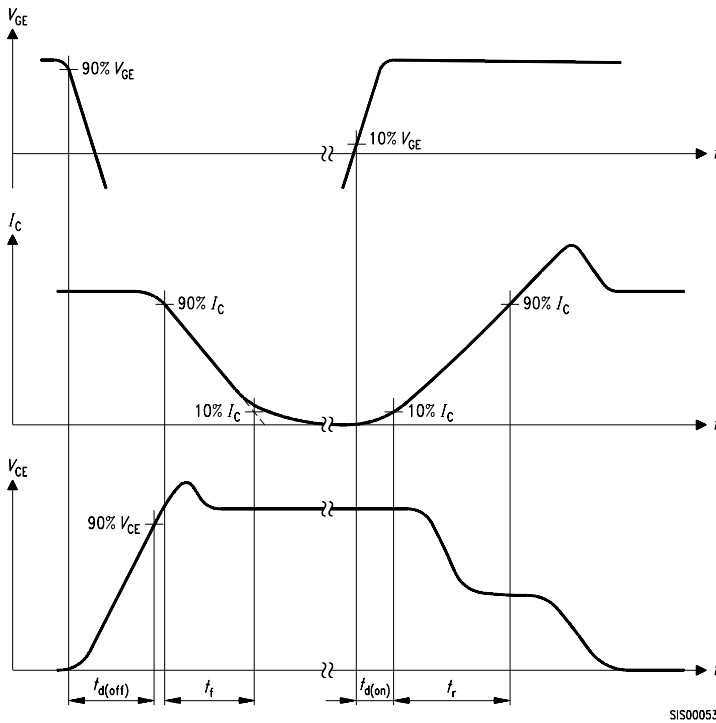


Figure A. Definition of switching times

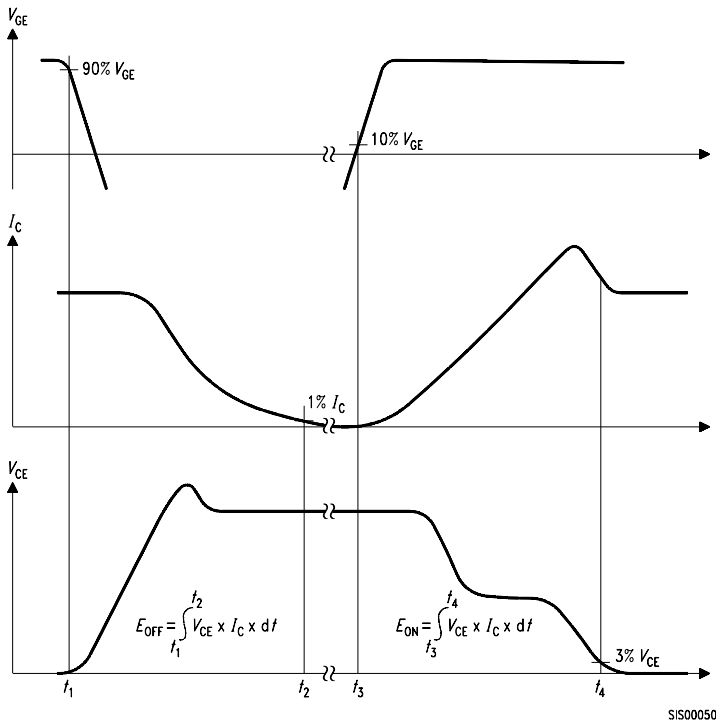


Figure B. Definition of switching losses

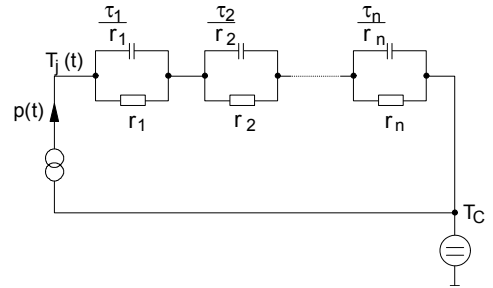


Figure D. Thermal equivalent circuit

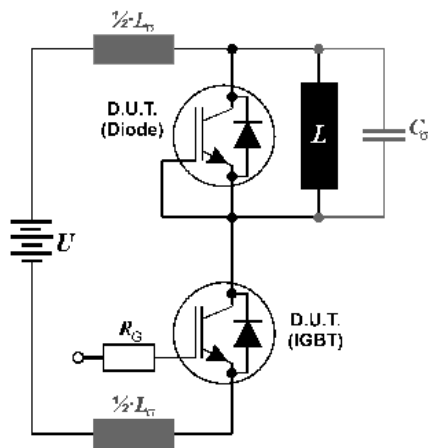


Figure E. Dynamic test circuit
Leakage inductance $L_\sigma = 180\text{nH}$
and Stray capacity $C_\sigma = 900\text{pF}$.

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